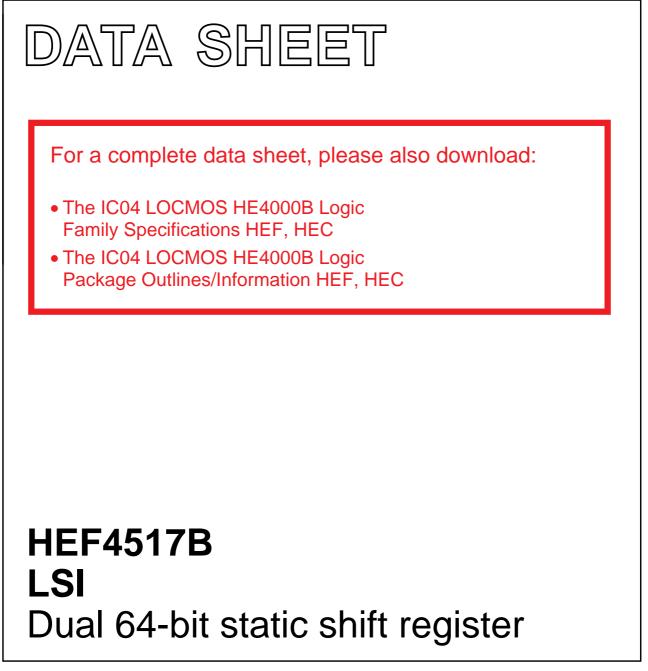
INTEGRATED CIRCUITS



Product specification File under Integrated Circuits, IC04 January 1995



HEF4517B

LSI

Dual 64-bit static shift register

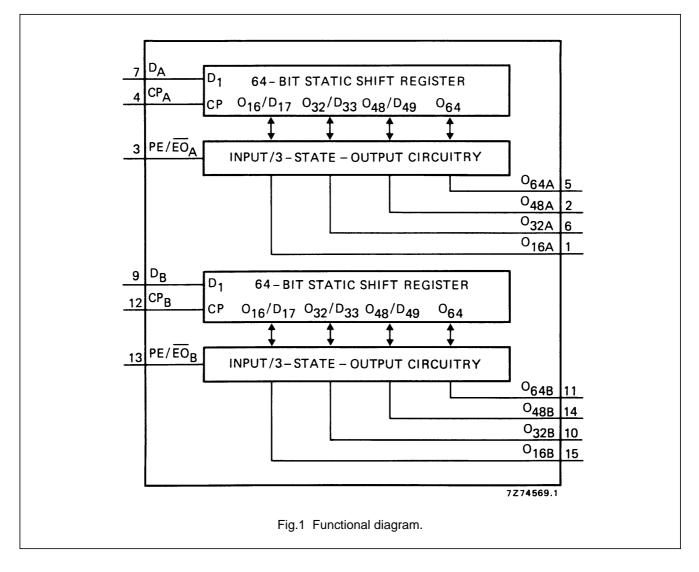
DESCRIPTION

The HEF4517B consists of two identical, independent 64-bit static shift registers. Each register has separate clock (CP), data input (D), parallel

input-enable/output-enable (PE/ \overline{EO}) and four 3-state outputs of the 16th, 32nd, 48th and 64th bit positions (O₁₆ to O₆₄). Data at the D input is entered into the first bit on the LOW to HIGH transition of the clock, regardless of the state of PE/ \overline{EO} .

When PE/\overline{EO} is LOW the outputs are enabled and the device is in the 64-bit serial mode.

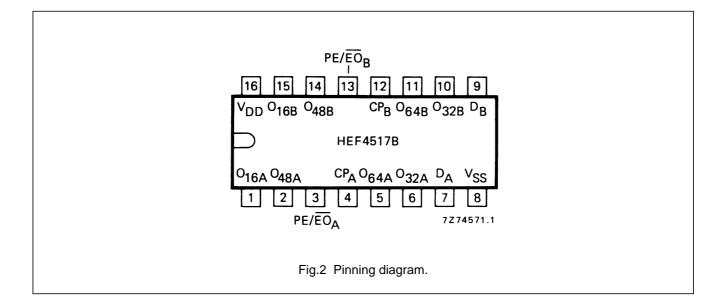
When PE/ \overline{EO} is HIGH the outputs are disabled (high impedance OFF-state), the 64-bit shift register is divided into four 16-bit shift registers with D, O₁₆, O₃₂ and O₄₈ as data inputs of the 1st, 17th, 33rd, and 49th bit respectively. Schmitt-trigger action in the clock input makes the circuit highly tolerant to slower clock rise and fall times.



FAMILY DATA, I_{DD} LIMITS category LSI

See Family Specifications

HEF4517B LSI

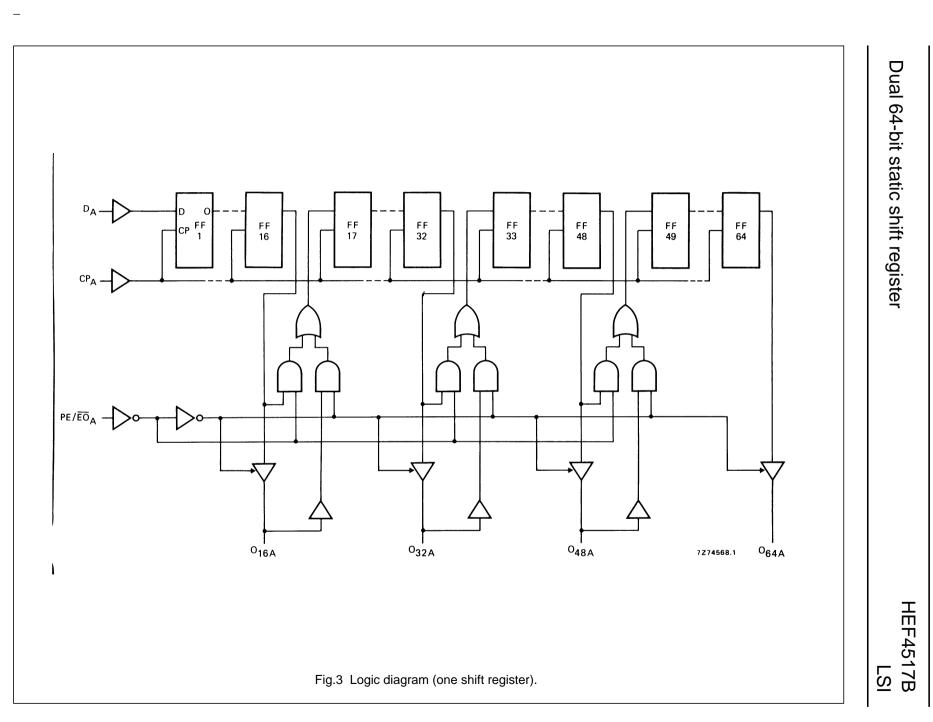


- HEF4517BP(N): 16-lead DIL; plastic (SOT38-1)
- HEF4517BD(F): 16-lead DIL; ceramic (cerdip) (SOT74)
- HEF4517BT(D): 16-lead SO; plastic (SOT109-1)
- (): Package Designator North America

PINNING

CP _A , CP _B	clock inputs
PE/\overline{EO}_A , PE/\overline{EO}_B	parallel input-enable/output-enable inputs
D _A , D _B	data inputs
O _{16A} , O _{32A} , O _{48A}	3-state outputs/inputs
O _{16B} , O _{32B} , O _{48B}	3-state outputs/inputs
O _{64A} , O _{64B}	3-state outputs

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Product specification

INPUTS			INPUTS/OUTPUTS				
СР	D	PE/EO	O ₁₆	O ₃₂	O ₄₈		
5	data entered into 1st bit	L	content of 16th bit displayed	content of 32nd bit displayed	content of 48th bit displayed		
5	data entered into 1st bit	Н	data at O_{16} entered	data at O_{32} entered into	data at O ₄₈ entere		

		displayed	displayed	displayed	displayed
ntered t bit	Н	data at O ₁₆ entered into 17th bit	data at O ₃₂ entered into 33rd bit	data at O_{48} entered into 49th bit	remains in 'Z' state
Х	L	no change	no change	no change	no change
Х	Н	Z	Z	Z	Z

Notes

сл

 \mathcal{L}

r

1. H = HIGH state (the more positive voltage)

L = LOW state (the less positive voltage)

X = state is immaterial

Z = high impedance state

 \checkmark = positive-going transition

 γ = negative-going transition

Philips Semiconductors

Product specification

MODE

One 64-bit shift

shift register is

Four 16-bit shift

no change

no change

register. The content of the

shifted over one stage

register. The content of the shift registers is shifted over one stage.

O64

content of

64th bit

_

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HEF4517B LSI

AC CHARACTERISTICS

 V_{SS} = 0 V; T_{amb} = 25 °C; input transition times \leq 20 ns

	V _{DD} V	TYPICAL FORMULA FOR P (μ W)	
Dynamic power	5	7 000 f _i + Σ (f _o C _L) × V _{DD} ²	where
dissipation per	10	28 000 f _i + Σ (f _o C _L) × V _{DD} ²	f _i = input freq. (MHz)
package (P)	15	70 000 f _i + Σ (f _o C _L) × V _{DD} ²	f _o = output freq. (MHz)
			C_L = load capacitance (pF)
			Σ (f _o C _L) = sum of outputs
			V _{DD} = supply voltage (V)

AC CHARACTERISTICS

 V_{SS} = 0 V; T_{amb} = 25 °C; C_L = 50 pF; input transition times \leq 20 ns

	V _{DD} V	SYMBOL	MIN.	TYP.	MAX.		TYPICAL EXTRAPOLATION FORMULA
Propagation delays							
$CP \to O_n$	5			220	440	ns	193 ns + (0,55 ns/pF) C _L
HIGH to LOW	10	t _{PHL}		85	170	ns	74 ns + (0,23 ns/pF) C _L
	15			60	120	ns	52 ns + (0,16 ns/pF) C _L
	5			190	380	ns	163 ns + (0,55 ns/pF) C _L
LOW to HIGH	10	t _{PLH}		75	150	ns	64 ns + (0,23 ns/pF) C _L
	15			50	100	ns	42 ns + (0,16 ns/pF) C _L
Output transition							
times	5			60	120	ns	10 ns + (1,0 ns/pF) C _L
HIGH to LOW	10	t _{THL}		30	60	ns	9 ns + (0,42 ns/pF) C _L
	15			20	40	ns	6 ns + (0,28 ns/pF) C _L
	5			60	120	ns	10 ns + (1,0 ns/pF) C _L
LOW to HIGH	10	t _{TLH}		30	60	ns	9 ns + (0,42 ns/pF) C _L
	15			20	40	ns	6 ns + (0,28 ns/pF) C _L

HEF4517B LSI

AC CHARACTERISTICS

 V_{SS} = 0 V; T_{amb} = 25 °C; C_L = 50 pF; input transition times \leq 20 ns

	V _{DD} V	SYMBOL	MIN.	TYP.	MAX.		
Minimum clock	5			95	190	ns	
pulse width; LOW	10	t _{WCPL}		40	80	ns	
	15			30	60	ns	
Set-up times	5		30	10		ns	
$O_n, D \rightarrow CP$	10	t _{su}	25	5		ns	see also waveforms Fig.4.
	15		20	5		ns	1 19.4.
Hold time	5		45	15		ns	
$O_n, D \rightarrow CP$	10	t _{hold}	30	10		ns	
	15		25	10		ns	
3-state propagation							
delays							
Output disable times							
$PE/\overline{EO} \rightarrow O_n$	5			40	80	ns	
HIGH	10	t _{PHZ}		30	60	ns	
	15			25	50	ns	
	5			50	100	ns	
LOW	10	t _{PLZ}		30	60	ns	
	15			25	50	ns	
Output enable times							
$PE/\overline{EO} \rightarrow O_n$	5			45	90	ns	
HIGH	10	t _{PZH}		25	50	ns	
	15			20	40	ns	
	5			60	120	ns	
LOW	10	t _{PZL}		30	60	ns	
	15			25	50	ns	
Maximum clock	5		2	5		MHz	
pulse frequency	10	f _{max}	6	12		MHz	
	15		8	16		MHz	

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